

N-channel TrenchMOS logic level FET

Rev. 02 — 9 March 2010

**Product data sheet** 

Suitable for logic level gate drive

Switched-mode power supplies

sources

#### **Product profile** 1.

## 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

## 1.2 Features and benefits

Simple gate drive required due to low gate charge

## 1.3 Applications

DC-to-DC convertors

# 1.4 Quick reference data

#### Table 1. Symbol Parameter Conditions Min Тур Max Unit T<sub>i</sub> ≥ 25 °C; T<sub>i</sub> ≤ 175 °C ٧ VDS drain-source voltage 30 \_ \_ drain current $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ 75 А $I_D$ see Figure 1 and 3 **P**<sub>tot</sub> total power dissipation T<sub>mb</sub> = 25 °C; see Figure 2 120 W --**Dynamic characteristics** $V_{GS} = 5 \text{ V}; \text{ I}_{D} = 50 \text{ A};$ gate-drain charge 4.6 nC Q<sub>GD</sub> \_ V<sub>DS</sub> = 15 V; T<sub>i</sub> = 25 °C; see Figure 11 Static characteristics 10 $R_{\text{DSon}}$ drain-source on-state $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ 8 mΩ -T<sub>i</sub> = 25 °C; see Figure 9 resistance

#### **Quick reference**



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# 2. Pinning information

Table 2.	Pinning	information				
Pin	Symbol	Description		Simplified outline	Graphic symbol	
1	G	gate			_	
2	D	drain	<u>[1]</u>	mb		
3	S	source				
mb	D	mounting base; connected to drain			mbb076 S	
				SOT428 (DPAK)		

[1] It is not possible to make a connection to pin 2.

# 3. Ordering information

#### Table 3.Ordering information

Type number	Package				
	Name	Description	Version		
PHD71NQ03LT	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

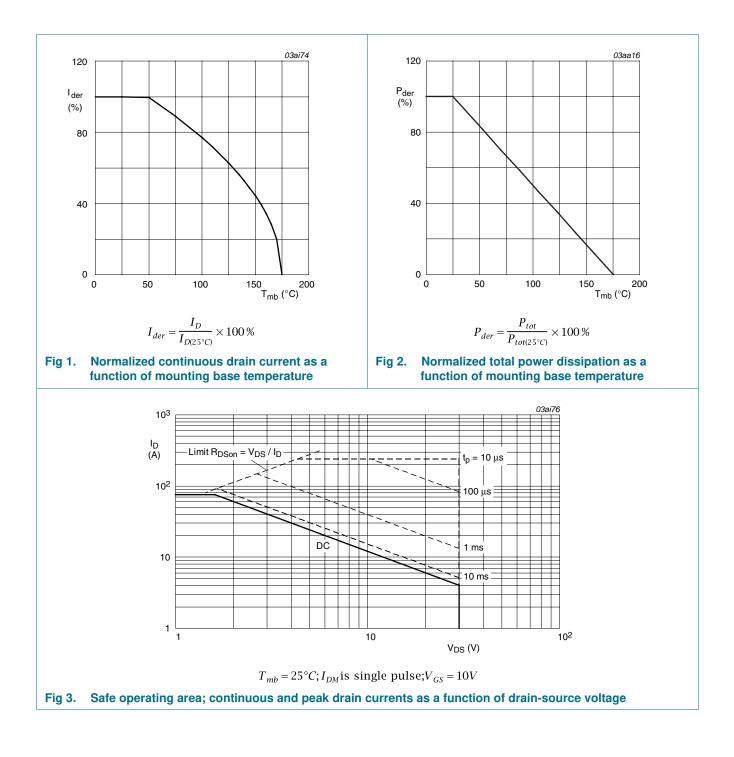
# 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	57.5	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u> and <u>3</u>	-	75	А
I <sub>DM</sub>	peak drain current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	240	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	120	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$V_{GSM}$	peak gate-source voltage	pulsed; $\delta$ = 25 %; $t_p$ ≤ 50 $\mu s$	-25	25	V
Source-di	rain diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	75	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	57.7	А

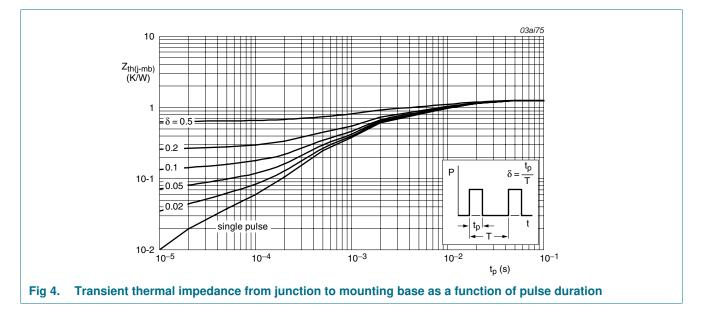
# PHD71NQ03LT



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#### **Thermal characteristics** 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.25	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	75	-	K/W

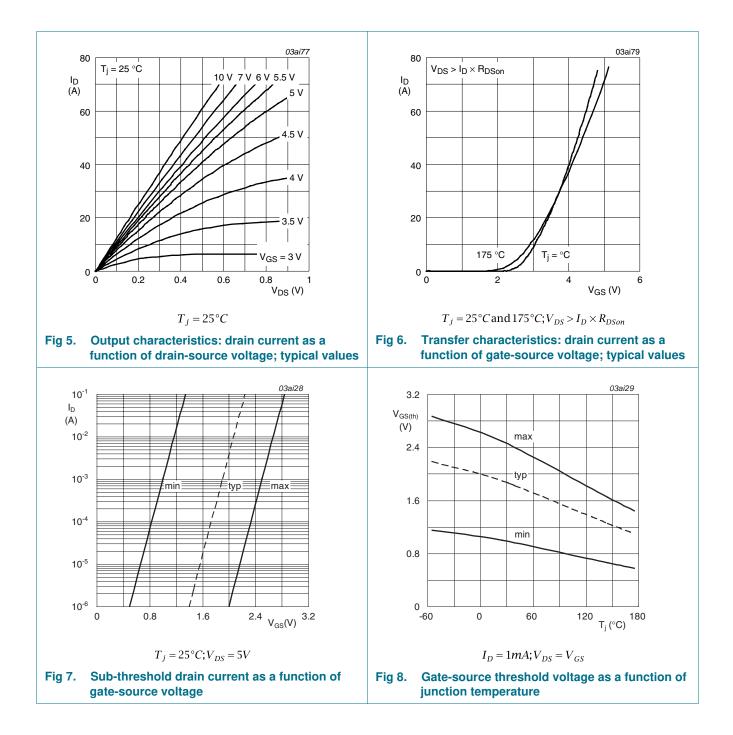


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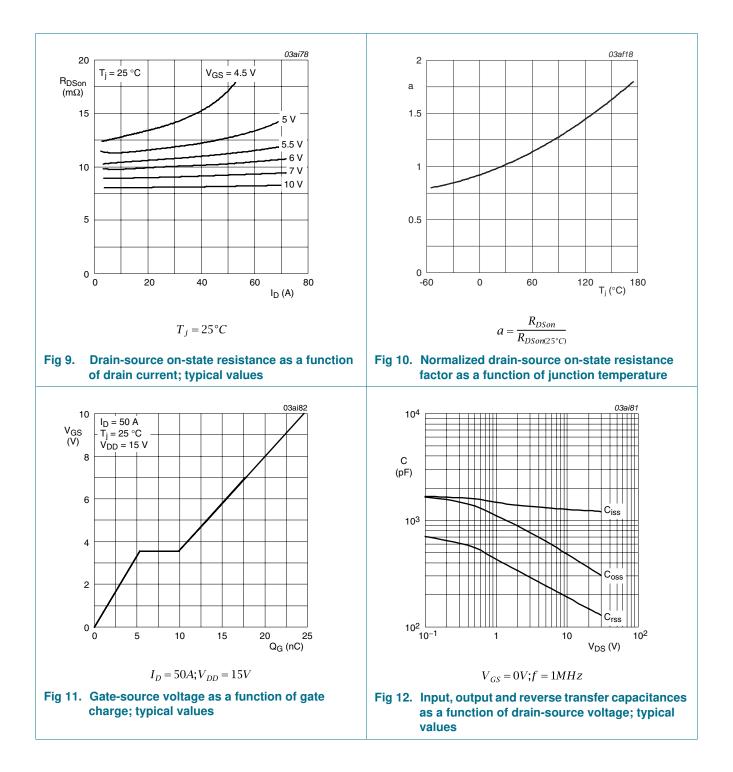
# 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	27	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	30	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; \text{see } \frac{\text{Figure 8}}{1000 \text{ Figure 8}}$	0.6	-	-	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; \text{see } \frac{\text{Figure 8}}{\text{Figure 8}}$	-	-	2.9	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; \text{see } \frac{\text{Figure 8}}{1000 \text{ Figure 8}}$	1	1.9	2.5	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 5 V; $I_{D}$ = 25 A; $T_{j}$ = 175 °C; see Figure 9 and $\underline{10}$	-	21.6	27.4	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 9</u>	-	8	10	mΩ
		$V_{GS}$ = 5 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 9</u> and <u>10</u>	-	12	15.2	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 50 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 5 \text{ V}; T_j = 25 \text{ °C};$	-	13.2	-	nC
Q <sub>GS</sub>	gate-source charge	see <u>Figure 11</u>		5.3	-	nC
Q <sub>GD</sub>	gate-drain charge		-	4.6	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ °C};$	-	1220	-	pF
C <sub>oss</sub>	output capacitance	see Figure 12	-	330	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	140	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_L$ = 0.6 Ω; $V_{GS}$ = 4.5 V;	-	15	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \ \Omega; T_j = 25 \ ^{\circ}C; I_D = 25 \ A$	-	150	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	13.5	-	ns
t <sub>f</sub>	fall time		-	18	-	ns
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{100000000000000000000000000000000000$	-	0.9	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	29	-	ns
Qr	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C	-	20	-	nC

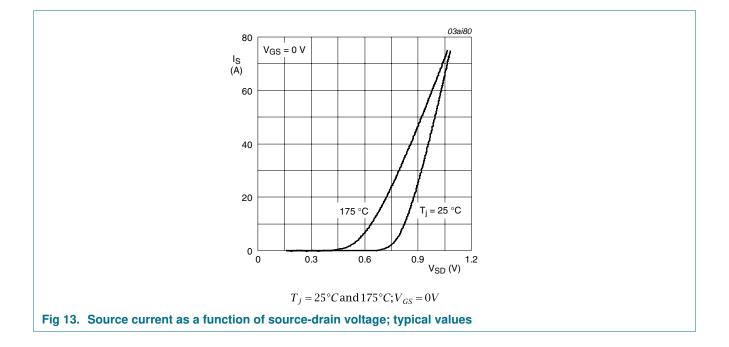
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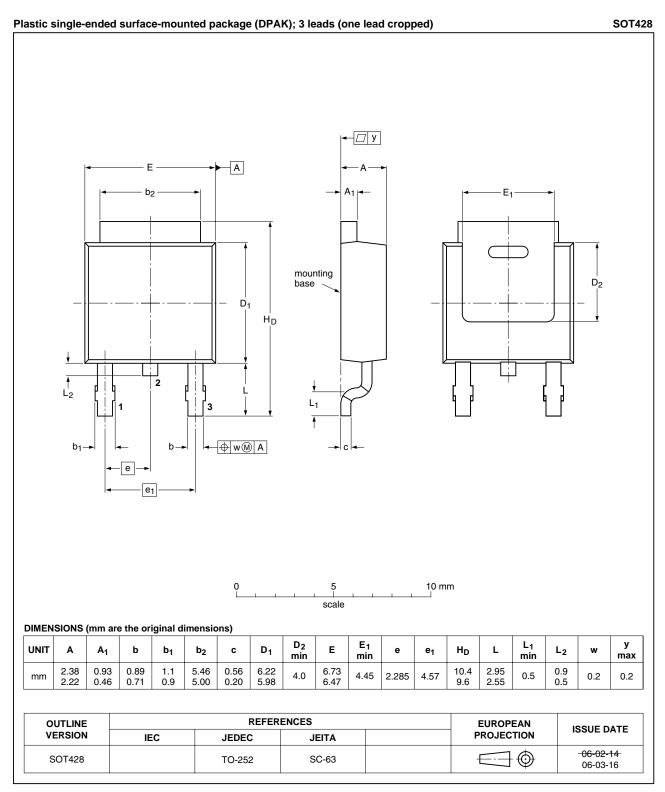


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# 7. Package outline



#### Fig 14. Package outline SOT428 (DPAK)

PHD71NQ03LT\_2 Product data sheet

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# 8. Revision history

Table 7.Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PHD71NQ03LT_2	20100309	Product data sheet	-	PHP_PHB_PHD71NQ03LT-01		
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>					
	<ul> <li>Legal texts</li> </ul>	have been adapted to	the new company	name where appropriate.		
		per PHD71NQ03LT sep _PHD71NQ03LT-01.	parated from data s	heet		
PHP_PHB_PHD71NQ03LT-01	20020625	Product data	-	-		

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# 9. Legal information

### 9.1 Data sheet status

Document status [1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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